



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

2813
#5/A
8/30/02
Mousi

In re the Application of:

YASUMOTO, Tamihide

Group Art Unit: 2813

Serial No.: 09/995,575

Examiner: **KIELIN, E.**

Filed: **November 29, 2001**

P.T.O. Confirmation No.: 1497

For: **SEMICONDUCTOR DEVICE MANUFACTURING METHOD USING METAL SILICIDE REACTION AFTER ION IMPLANTATION IN SILICON WIRING**

AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

August 20, 2002

Sir:

In response to the Office Action dated June 5, 2002, please amend the above-identified application as follows:

IN THE ABSTRACT:

A1
LAST
PAGE

✓ Please delete the current Abstract and replace therewith the attached substitute Abstract.

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IN THE SPECIFICATION:

Please replace the paragraph at page 2, lines 13-23 with the following rewritten paragraph:

A2
According to one aspect of the present invention, there is provided a method for manufacturing a semiconductor device, comprising the steps of: forming a wiring comprising silicon on a surface of a semiconductor substrate; covering part of the wiring with a resist pattern; implanting ions into the wiring